



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	30V
I_D	5.6A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	25mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	31mohm
$R_{DS(ON)}$ (at $V_{GS}=2.5V$)	45mohm

General Description

Trench Power LV MOSFET technology
 High density cell design for low $R_{DS(ON)}$
 High Speed switching
 Moisture Sensitivity Level 1
 Epoxy Meets UL 94 V-0 Flammability Rating
 Halogen Free

Applications

Battery protection
 Load switch
 Power management

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	30	V
Gate-source Voltage		V_{GS}	± 12	V
Drain Current	$T_A=25$	I_D	5.6	A
	$T_A=70$		4.5	



YJL3400A

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FOR NEW DESIGN

YJL3400A

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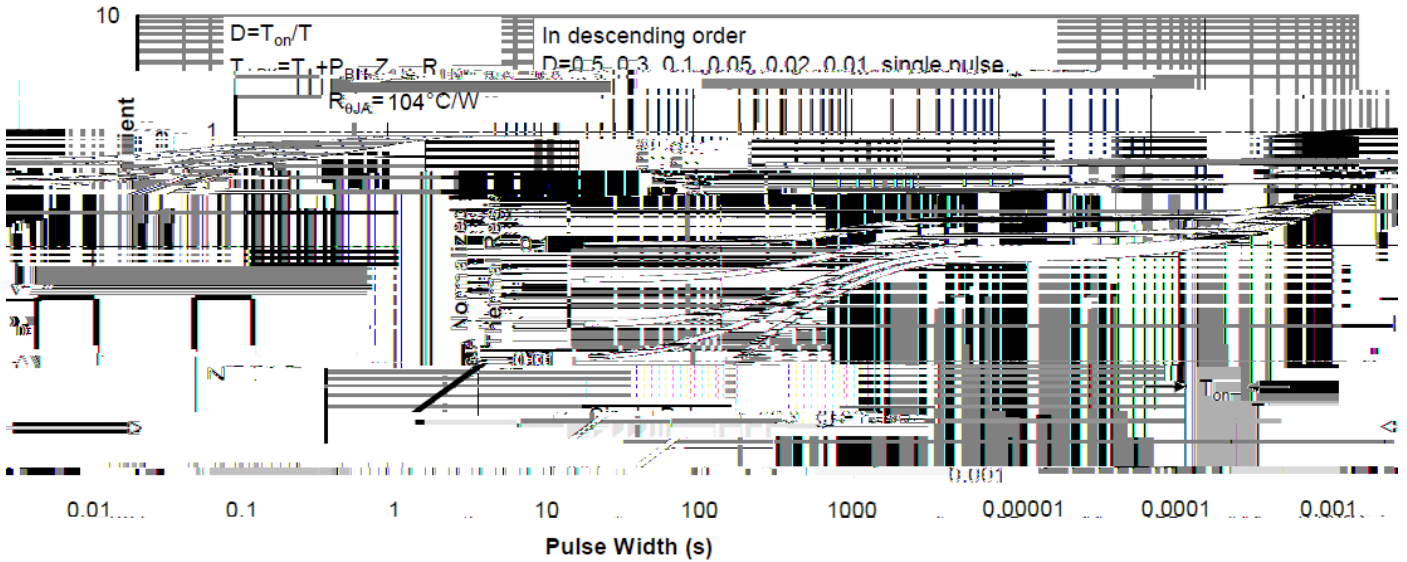
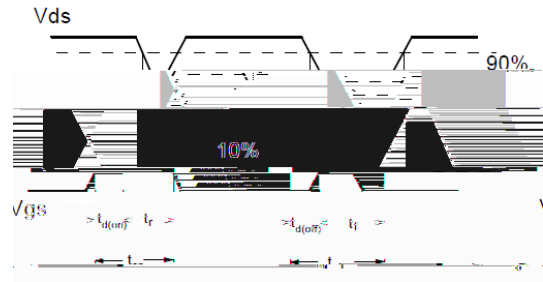
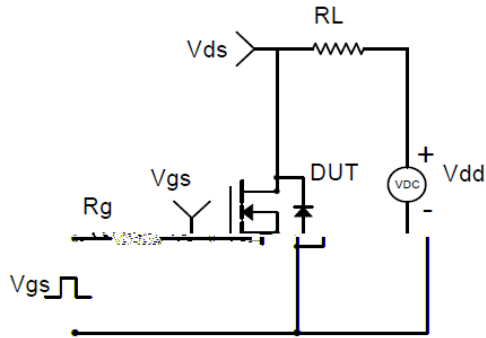
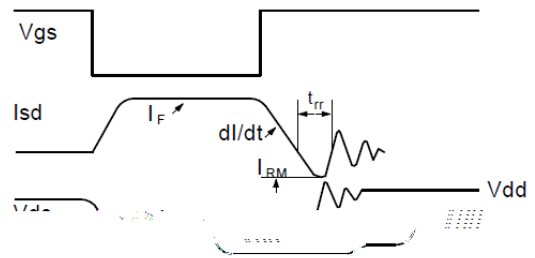
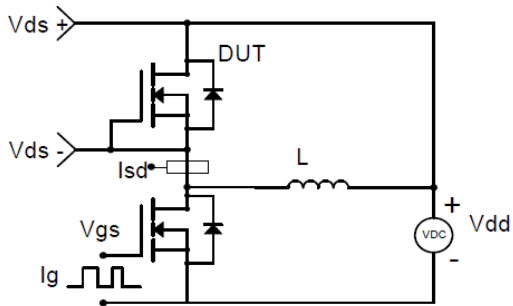


Figure13. Normalized Maximum Transient Thermal Impedance



Resistive Switching Test Circuit & Waveforms



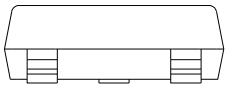
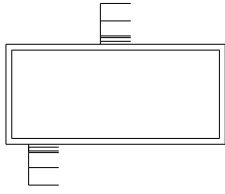
Diode Recovery Test Circuit



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SOT-23 Package information



UNIT mm

NOT RECOMMENDED
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Disclaimer

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